Ficha de investigador

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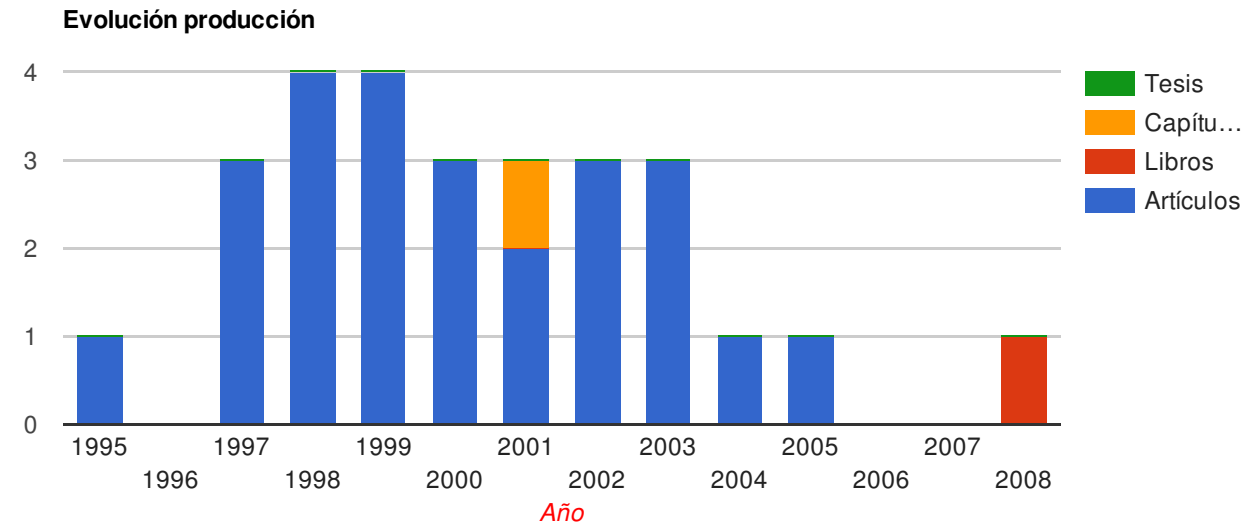
Ficha del Directorio

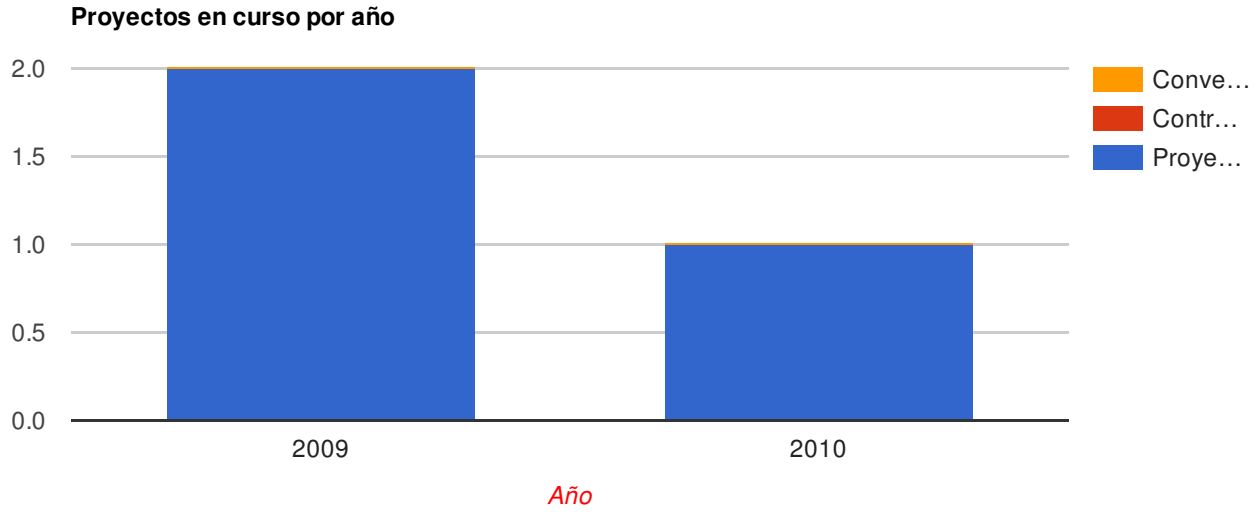
Producción 27

Artículos (25) Libros (1) Capítulos de Libros (1) Tesis dirigidas (0)



Proyectos dirigidos 2

Proyectos (2) Contratos (0) Convenios (0)



Actividades 0

Titulo publicación	Fuente	Tipo	Fecha
Nuevas tecnologías en los dispositivos electrónicos	Departamento de electrónica y tecnología de computadores	Libros	2008
Influence of confined acoustic phonons on the electron mobility in ultrathin silicon-oninsulator layers	Ecs transactions	Articulo	2005
Image and exchange-correlation effects in double gate silicon-on-insulator transistors	Microelectronic engineering	Articulo	2004
Electron mobility in double gate silicon on insulator transistors: symmetric-gate versus asymmetric-gate configuration	Journal of applied physics	Articulo	2003
Influence of image force and many-body correction on electron mobility in ultrathin double gate silicon on insulator inversion layers	Applied physics letters	Articulo	2003
Strained-si on si1-xgex mosfet mobility model	Ieee transactions on electron devices	Articulo	2003
Coulomb scattering model for ultrathin silicon-on-insulator inversion layers	Applied physics letters	Articulo	2002
Electron transport in strained si inversion layers grown on sige-on-insulator substrates	Journal of applied physics	Articulo	2002
Monte carlo simulation of electron mobility in silicon-on-insulator structures	Solid-state electronics	Articulo	2002
Electron transport in silicon-on-insulator devices	Solid-state electronics	Articulo	2001
Monte carlo simulation of electron transport in silicon-on-insulator devices	Silicon on insulator. technology and devices x	Capítulo de libro	2001
Role of surface-roughness scattering in double gate silicon-on-insulator inversion layers	Journal of applied physics	Articulo	2001
Deep submicrometer soi mosfet drain current model including series resistance, self-heating and velocity overshoot effects	Ieee electron device letters	Articulo	2000
Effects of the inversion-layer centroid on the performance of double-gate mosfet's	Ieee transactions on electron devices	Articulo	2000
Semiempirical closed-form models for the inversion-layer centroid of a p-mos including quantum effects	Semiconductor science and technology	Articulo	2000
A computational study of the strained-si mosfet: a possible alternative for the next century electronics industry	Computer physics communications	Articulo	1999
Electron mobility in extremely thin single-gate silicon-on-insulator inversion layers	Journal of applied physics	Articulo	1999
Experimental determination of the effective mobility in nmosfets: a comparative study	Solid-state electronics	Articulo	1999
Surface roughness at the si-sio2 interfaces in fully depleted silicon-on-insulator inversion layers	Journal of applied physics	Articulo	1999
2-dimensional drift-diffusion simulation of superficial strained-si/si1-xgex channel metal-oxide-semiconductor field-effect transistors		Articulo	1998
A model for the drain current of deep submicrometer mosfet's including electron-velocity overshoot	Ieee transactions on electron devices	Articulo	1998
Electron-mobility in quantized beta-sic inversion-layers		Articulo	1998
Monte carlo simulation of electron transport properties in extremely thin soi mosfet's	Ieee transactions on electron devices	Articulo	1998
Effects of the inversion layer centroid on mosfet behavior	Ieee transactions on electron devices	Articulo	1997
Electron transport properties of quantized silicon carbide inversion layers	Journal of electronic materials	Articulo	1997
The dependence of the electron-mobility on the longitudinal	Semiconductor science and	Articulo	1997

electric-field in mosfets	technology		
Universality of electron-mobility curves in mosfets - a monte-carlo study	Ieee transactions on electron devices	Articulo	1995

	Titulo proyecto	Tipo	Inicio	Fin
1	Dotación de un laboratorio redes de computadores y formación del profesorado de la carrera profesional ingeniería informática y sistemas de la universidad nacional micaela bastidas apurímac - perú	Proyecto	8/1/09	7/31/10
2	Dotación de un laboratorio de electrónica y formación del profesorado en técnicas de instrumentación	Proyecto	4/1/09	9/30/09

Actividades 0

Titulo actividad	Fuente	Tipo	Fecha

Colaboradores

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- JUAN ENRIQUE CARCELLER BELTRAN (16)
- FRANCISCO JIMENEZ MOLINOS (7)
- SALVADOR RODRIGUEZ BOLIVAR (5)
- JESUS BANQUERI OZAEZ (4)
- ANDRES GODOY MEDINA (3)
- ANDRÉS MARÍA ROLDÁN ARANDA (3)
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- ALBERTO JOSE PALMA LOPEZ (1)
- JUAN ANTONIO JIMENEZ TEJADA (1)